



JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

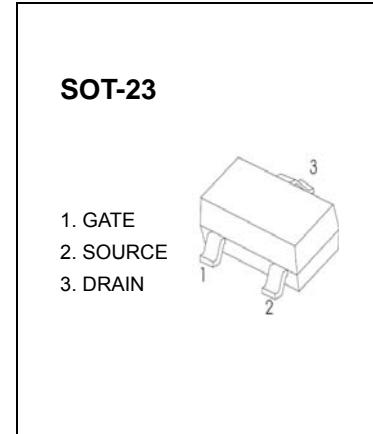
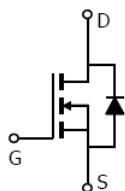
SOT-23 Plastic-Encapsulate Transistors

CJ3420 N-Channel Enhancement Mode Field Effect Transistor

DESCRIPTION

The CJ3420 uses advanced trench technology to provide excellent $R_{DS(on)}$. This device is suitable for use as a uni-directional or bi-directional load switch.

MARKING: R20



Maximum ratings ($T_a=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	20	V
Gate-Source Voltage	V_{GS}	± 12	
Continuous Drain Current	I_D	6	A
Pulsed Drain Current	I_{DM}	25	
Maximum Body-Diode Continuous Current	I_S	2	
Power Dissipation	P_D	0.35	W
Thermal Resistance from Junction to Ambient	$R_{\theta JA}$	357	°C/W
Junction Temperature	T_J	150	°C
Storage Temperature	T_{stg}	-55 ~ +150	

Electrical characteristics ($T_a=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
STATIC PARAMETERS						
Drain-source breakdown voltage	$V_{(\text{BR})\text{DSS}}$	$V_{\text{GS}} = 0\text{V}, I_{\text{D}} = 250\mu\text{A}$	20			V
Gate-source leakage current	I_{GSS}	$V_{\text{DS}} = 0\text{V}, V_{\text{GS}} = \pm 12\text{V}$			± 100	nA
Zero gate voltage drain current	I_{DSS}	$V_{\text{DS}} = 16\text{V}, V_{\text{GS}} = 0\text{V}$			1.0	μA
Gate threshold voltage	$V_{\text{GS}(\text{th})}$	$V_{\text{DS}} = V_{\text{GS}}, I_{\text{D}} = 250\mu\text{A}$	0.5	0.7	1.0	V
Drain-source on-state resistance	$R_{\text{DS}(\text{on})}$	$V_{\text{GS}} = 10\text{V}, I_{\text{D}} = 6.0\text{A}$		19	24	$\text{m}\Omega$
		$V_{\text{GS}} = 4.5\text{V}, I_{\text{D}} = 5.0\text{A}$		22	27	
		$V_{\text{GS}} = 2.5\text{V}, I_{\text{D}} = 4.0\text{A}$		35	42	
		$V_{\text{GS}} = 1.8\text{V}, I_{\text{D}} = 2.0\text{A}$			74	
Diode forward voltage	V_{SD}	$V_{\text{GS}} = 0\text{V}, I_{\text{S}} = 1\text{A}$		0.75	1	V
Forward transconductance	g_{fs}	$V_{\text{DS}} = 5\text{V}, I_{\text{D}} = 3.8\text{A}$	4			S
DYNAMIC PARAMETERS*						
Input capacitance	C_{iss}	$V_{\text{DS}} = 10\text{V}, V_{\text{GS}} = 0\text{V}, f = 1\text{MHz}$		630		pF
Output capacitance	C_{oss}			164		
Reverse transfer capacitance	C_{rss}			137		
Gate resistance	R_g	$V_{\text{DS}} = 0\text{V}, V_{\text{GS}} = 0\text{V}, f = 1\text{MHz}$		1.5		Ω
SWITCHING PARAMETERS*						
Turn-on delay time	$t_{\text{d}(\text{on})}$	$V_{\text{GS}} = 5\text{V}, V_{\text{DS}} = 10\text{V}, R_L = 1.7\Omega, R_{\text{GEN}} = 6\Omega$		5.5		ns
Rise time	t_r			14		
Turn-off delay time	$t_{\text{d}(\text{off})}$			29		
Fall time	t_f			10.2		

*These parameters have no way to verify.

Typical Characteristics

CJ3420

